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electrode that covers substantially an entire surface of a light-emitting layer of the light-emitting element, and the positive electrode reflecting light emitted from the light-emitting layer toward the light-emitting layer, such that the light passes through the substrate and the transparent base.

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Sub  
D27

19. (Twice amended) A pair of lead frames for use in a light-emitting apparatus of flip chip bonding type comprising:

C2  
a transparent base having on a first surface thereof a first and a second bonding pad and  
a GaN semiconductor light-emitting device fixed on the first surface thereof,  
wherein a first lead frame has a first mount which faces the dominant light emitting direction of the light-emitting apparatus and on which the first bonding pad is to be fixed, and a second lead frame has a second mount which faces the dominant light emitting direction and on which the second bonding pad is to be fixed, the light-emitting device including a substrate and a positive electrode that covers substantially an entire surface of a light-emitting layer of the light-emitting device, and the positive electrode reflecting light emitted from the light-emitting layer toward the light-emitting layer, such that the light passes through the substrate and the transparent base.

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D37

21. (Twice amended) A light-emitting diode comprising:

C3  
a sapphire substrate;  
a light emitting layer made of GaN semiconductor and formed on said sapphire substrate; and

a positive electrode and a negative electrode formed on a surface of said light emitting layer on which the sapphire substrate is not formed;

wherein:

C3  
said positive electrode and said negative electrode are supplied with electricity through a wire, and

said positive electrode reflects light from said light emitting layer toward said sapphire substrate and covers substantially an entire surface of the light-emitting layer.

Please add new claims 22, 23, 24 and 25 as follows:

C4  
22. (New) A semiconductor light-emitting apparatus of flip chip bonding type as claimed in claim 14, wherein the light-emitting layer comprises a multi-quantum well layer.

23. (New) A pair of lead frames for use in a light-emitting apparatus of flip chip bonding type as claimed in claim 19, wherein the light-emitting layer comprises a multi-quantum well layer.

24. (New) A light-emitting diode as claimed in claim 21, wherein the light-emitting layer comprises a multi-quantum well layer.

25. (New) A light-emitting diode as claimed in claim 21, further comprising a layer containing a fluorescent material formed on a side of the sapphire substrate.